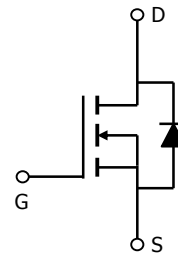


General Description

The AOD4132 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate resistance. This device is ideally suited for use as a low side switch in CPU core power conversion.

Features

$V_{DS} (V) = 30V$
 $I_D = 85A (V_{GS} = 10V)$
 $R_{DS(ON)} < 4m\Omega (V_{GS} = 10V)$
 $R_{DS(ON)} < 6m\Omega (V_{GS} = 4.5V)$



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^{B,G}	$T_C=25^\circ\text{C}$ ^G	85	A
	$T_C=100^\circ\text{C}$ ^B	63	
Pulsed Drain Current	I_{DM}	200	
Avalanche Current ^C	I_{AR}	30	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	112	mJ
Power Dissipation ^B	$T_C=25^\circ\text{C}$	100	W
	$T_C=100^\circ\text{C}$	50	
Power Dissipation ^A	$T_A=25^\circ\text{C}$	2.5	W
	$T_A=70^\circ\text{C}$	1.6	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	14.2	20	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A		39	50	$^\circ\text{C/W}$
Maximum Junction-to-Case ^C	$R_{\theta JC}$	0.8	1.5	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	1.8	3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	85			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=20\text{A}$ $T_J=125^\circ\text{C}$		2.8 4.4	4 5.5	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=20\text{A}$		4.4	6	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=20\text{A}$		106		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.72	1	V
I_S	Maximum Body-Diode Continuous Current				85	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		3700	4400	pF
C_{oss}	Output Capacitance			700		pF
C_{rss}	Reverse Transfer Capacitance			390		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		0.54	0.7	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=4.5\text{V}$, $V_{DS}=15\text{V}$, $I_D=20\text{A}$		63	76	nC
$Q_g(4.5\text{V})$	Total Gate Charge			33	40	nC
Q_{gs}	Gate Source Charge			8.6		nC
Q_{gd}	Gate Drain Charge			17.6		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=0.75\Omega$, $R_{GEN}=3\Omega$		12		ns
t_r	Turn-On Rise Time			15.5		ns
$t_{D(off)}$	Turn-Off DelayTime			40		ns
t_f	Turn-Off Fall Time			14		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=20\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		34	41	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=20\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		30		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on steady-state $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature to 175°C may be used if the PCB or heatsink allows it.

B: The power dissipation P_D is based on $T_{J(MAX)}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=175^\circ\text{C}$.

D: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F: These tests are performed with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

G: The maximum current rating is limited by the package current capability.

*This device is guaranteed green after data code 8X11 (Sep 1ST 2008).

Rev 1: Sep 2008

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

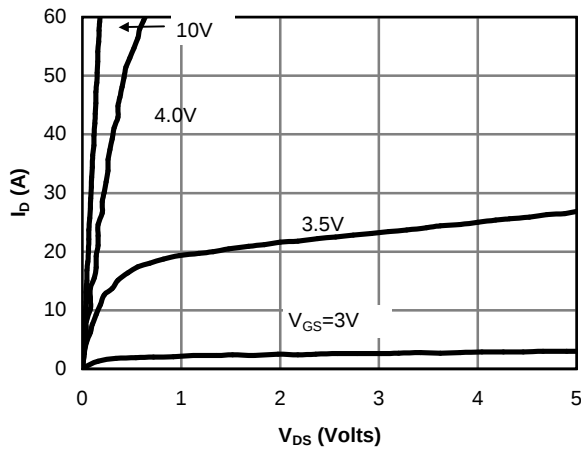


Fig 1: On-Region Characteristics

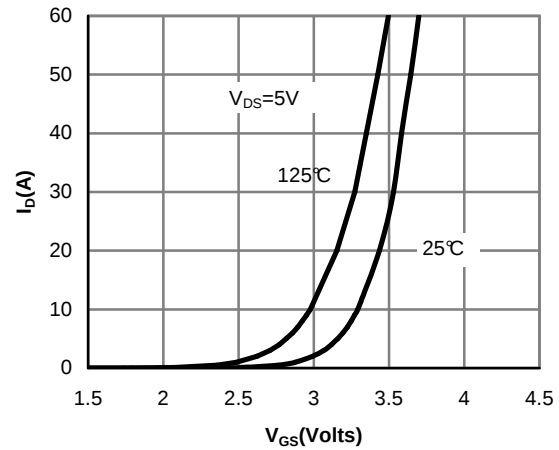


Figure 2: Transfer Characteristics

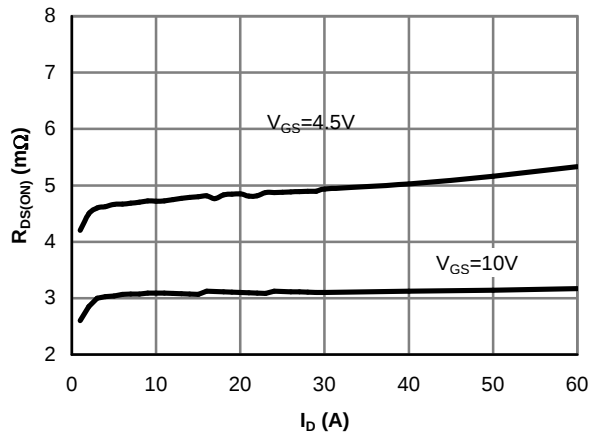


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

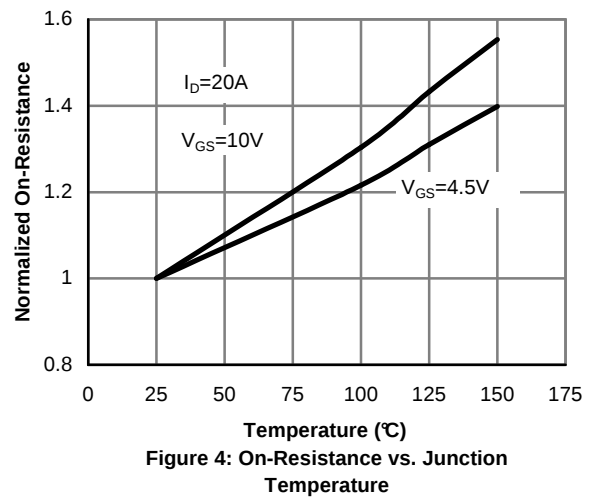


Figure 4: On-Resistance vs. Junction Temperature

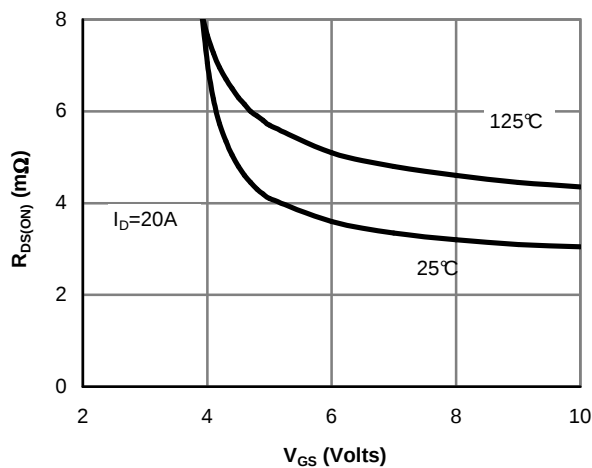


Figure 5: On-Resistance vs. Gate-Source Voltage

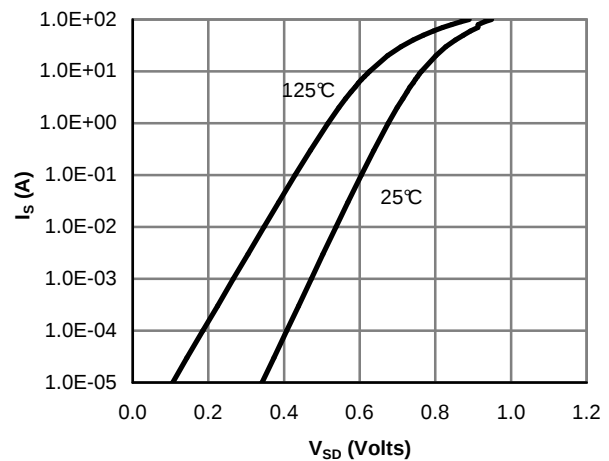
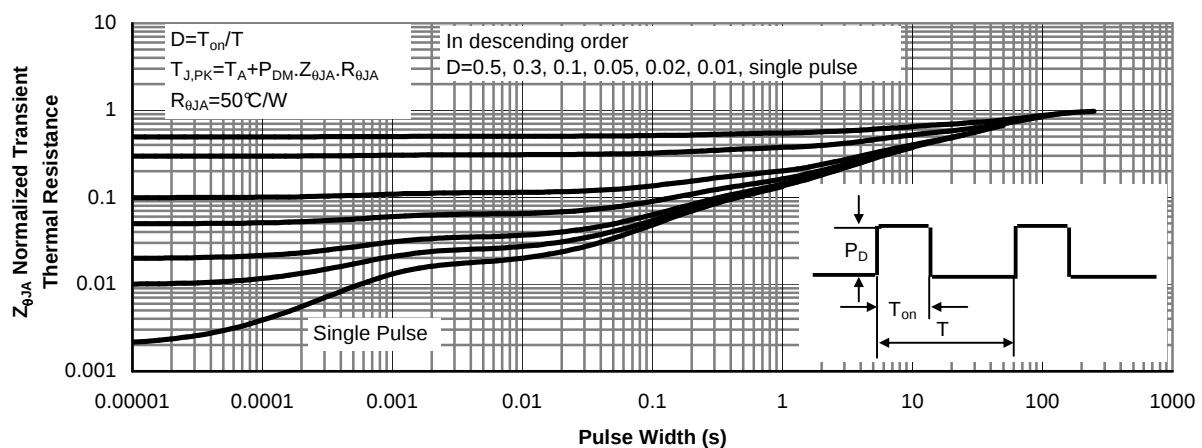
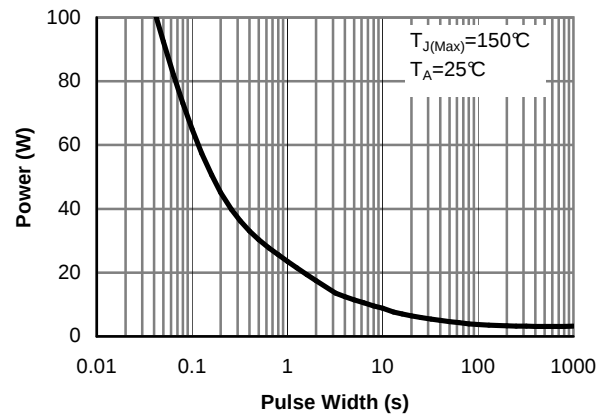
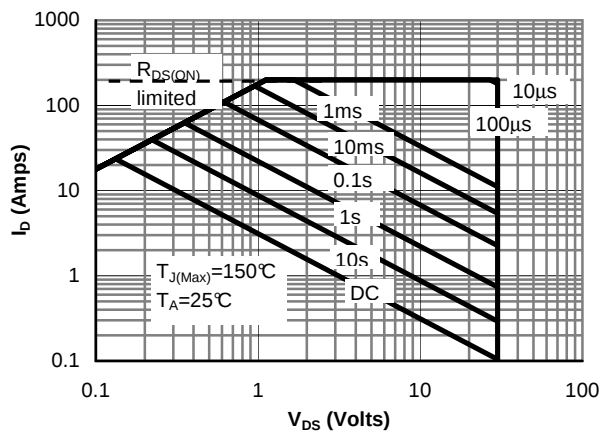
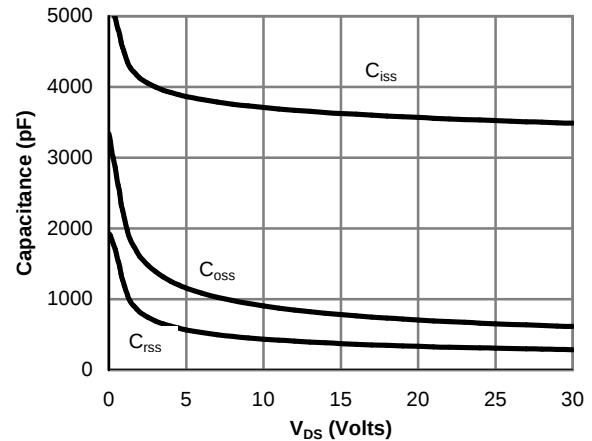
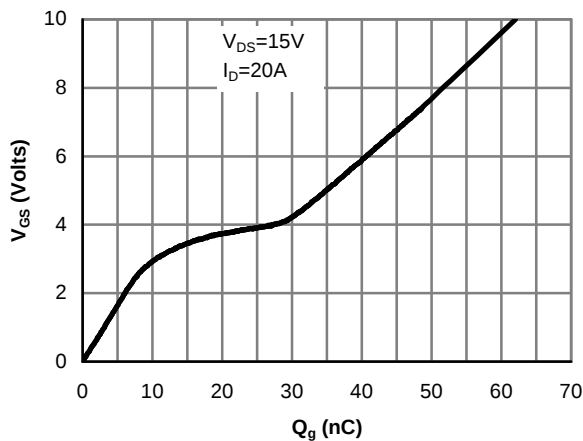
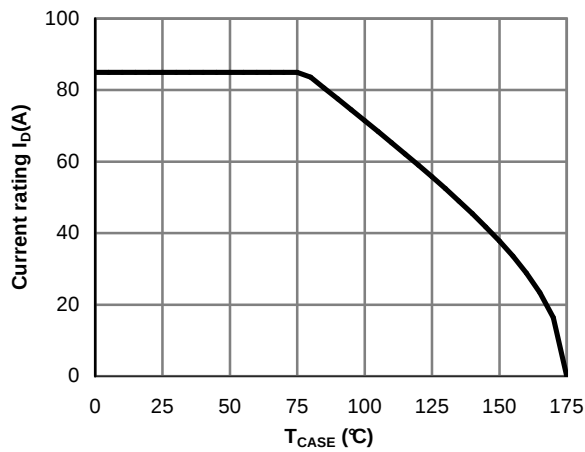
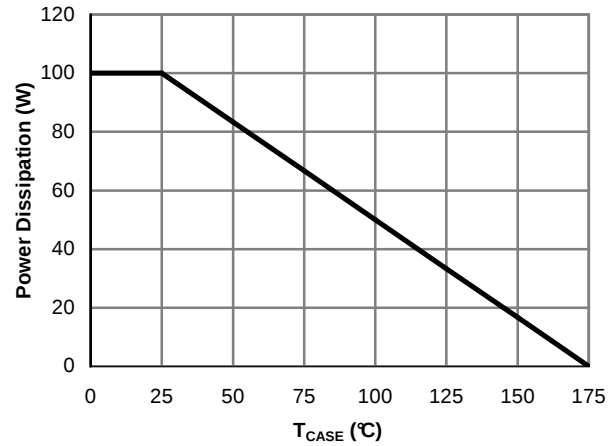
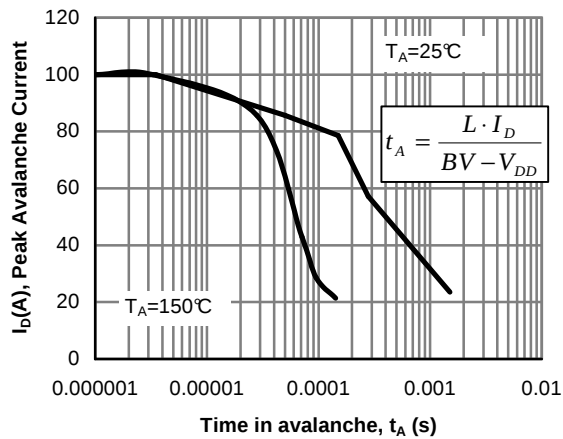


Figure 6: Body-Diode Characteristics

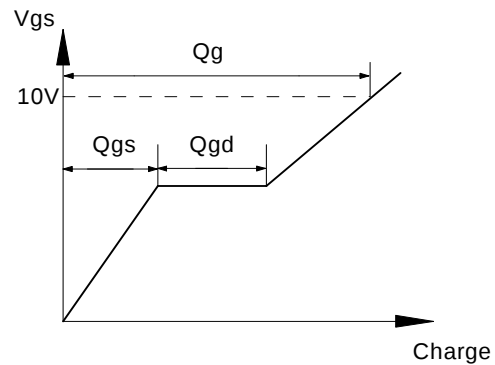
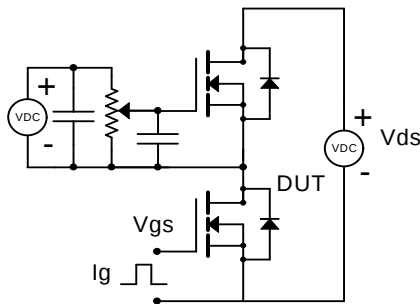
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



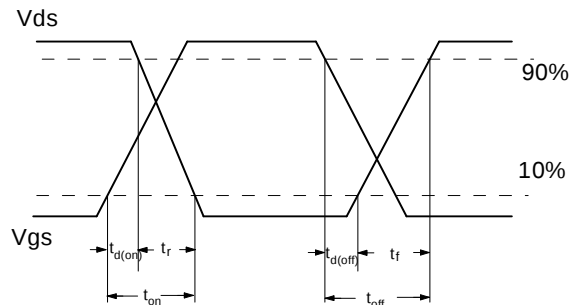
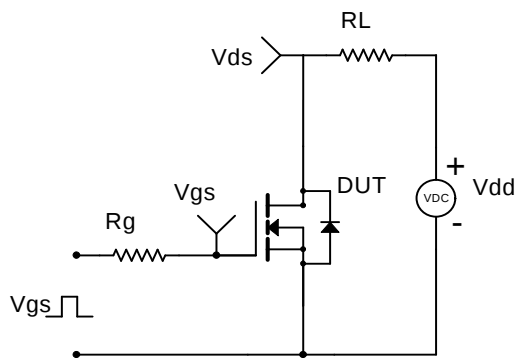
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



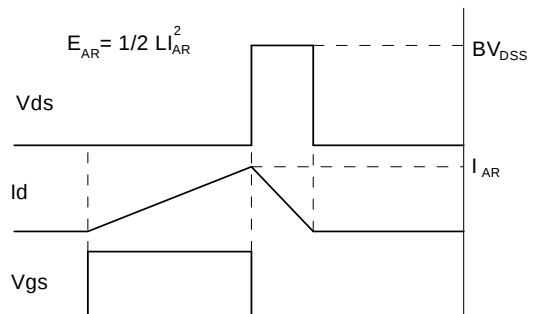
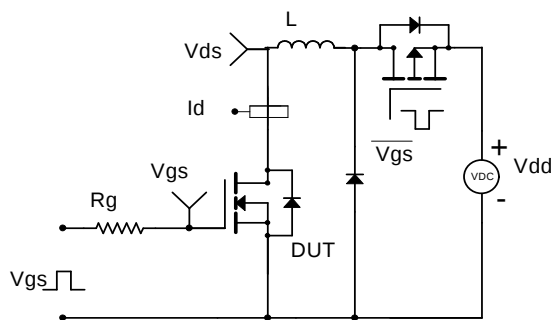
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

